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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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**Complete if Known**

Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Pham, Ly

Attorney Docket No: 1303.029US1

Sheet 1 of 2

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
LP	US-2003/0042527	03/06/2003	Forbes, Leonard, et al.	257	315	08/30/2001
	US-2003/0042532	03/06/2003	Forbes, Leonard	257	316	08/30/2001
	US-2003/0043622	03/06/2003	Forbes, Leonard	365	185.05	08/30/2001
	US-2003/0043630	03/06/2003	Forbes, Leonard, et al.	365	185.26	08/30/2001
	US-2003/0043632	03/06/2003	Forbes, Leonard	365	185.28	08/30/2001
	US-2003/0043633	03/06/2003	Forbes, Leonard, et al.	365	185.28	12/20/2001
	US-2003/0043637	03/06/2003	Forbes, Leonard, et al.	365	185.33	08/30/2001
	US-2003/0045082	03/06/2003	Eldridge, Jerome M., et al.	438	593	02/20/2002
	US-2003/0048666	03/13/2003	Eldridge, Jerome M., et al.	365	185.28	06/21/2002
	US-2004/0004245	01/08/2004	Forbes, Leonard, et al.	257	315	07/08/2002
	US-2004/0004247	01/08/2004	Forbes, Leonard, et al.	257	324	07/08/2002
	US-2004/0004859	01/08/2004	Forbes, Leonard, et al.	365	185.05	07/08/2002
	US-3,978,577	09/07/1976	Bhattacharyya, Arup, et al.	29	571	06/30/1975
	US-4,449,205	05/15/1984	Hoffman, Charles R.	365	182	02/19/1982
	US-4,495,219	01/22/1985	Kato, Takashi, et al.	427	82	10/08/1982
	US-4,717,943	01/05/1988	Wolf, Hans P., et al.	357	23.5	07/16/1986
	US-4,794,565	12/27/1988	Wu, Albert T., et al.	365	185	09/15/1986
	US-4,870,470	09/26/1989	Bass Jr., Roy S., et al.	357	23.5	10/16/1987
	US-5,445,984	08/29/1995	Gary, Hong, et al.	437	43	11/28/1994
	US-5,455,792	10/03/1995	Yi, Yong-Wan	365	185.12	09/09/1994
	US-5,510,278	04/23/1996	Bich-Yen, Nguyen, et al.	437	40	09/06/1994
	US-5,617,351	04/01/1997	Bertin, Claude L., et al.	365	185.05	06/05/1995
	US-5,646,430	07/08/1997	Kaya, Cetin, et al.	257	322	08/28/1995
	US-5,952,692	09/14/1999	Nakazato, Kazuo, et al.	257	321	10/28/1997

EXAMINER

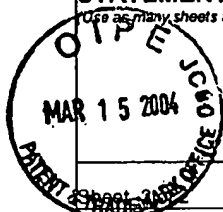
DATE CONSIDERED

04/03/04

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. † Applicant's unique citation designation number (optional). ‡ Applicant is to place a check mark here if English language translation is attached.

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Application Number	09/945500
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First Named Inventor	Forbes, Leonard
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Attorney Docket No: 1303.029US1	

LP	US-6,101,131	08/08/2000	Chang, Ming-Bing	365	185.33	04/22/1999
	US-6,127,227	10/03/2000	Lin, Chrong J., et al.	438	261	01/25/1999
	US-6,169,306	01/02/2001	Gardner, Mark I., et al.	257	310	07/27/1998
	US-6,288,419	09/11/2001	Prall, Kirk D., et al.	257	213	07/09/1999
	US-6,461,931	10/08/2002	Eldridge, Jerome M.	438	398	08/29/2000
	US-6,475,857	11/05/2002	Kim, Woosik, et al.	438	240	06/21/2001
↓	US-6,586,797	07/01/2003	Forbes, Leonard, et al.	257	325	08/30/2001

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Foreign Document No.	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>1</sup>
LP		BHATTACHARYYA, A., "Physical & Electrical Characteristics of LPCVD Silicon Rich Nitride", <u>ECS Technical Digest, J. Electrochem. Soc., 131(11), 691 RDP, New Orleans, (1984), 469C</u>	
		HAN, KWANGSEOK, "Characteristics of P-Channel Si Nano-Crystal Memory", <u>IEDM Technical Digest, International Electron Devices Meeting, (December 10-13, 2000), 309-312</u>	
		INUMIYA, S, et al., "Conformable formation of high quality ultra-thin amorphous Ta <sub>2</sub> O <sub>5</sub> gate dielectrics utilizing water assisted deposition (WAD) for sub 50 nm damascene metal gate MOSFETs", <u>IEDM Technical Digest, International Electron Devices Meeting, (December 10-13, 2000), 649-652</u>	
		MANCHANDA, L., "Si-doped aluminates for high temperature metal-gate CMOS: Zr-Al-Si-O, a novel gate dielectric for low power applications", <u>IEDM Technical Digest, International Electron Devices Meeting, (December 10-13, 2000), 23-26</u>	
		SHI, Y., "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", <u>IEEE Electron Device Letters, 19(10), (1998), pp. 388-390</u>	
		YAMAGUCHI, TAKESHI, "Band Diagram and Carrier Conduction Mechanism in ZrO <sub>2</sub> /Zr-silicate/Si MIS Structure Fabricated by Pulsed-laser-ablation Deposition", <u>Electron Devices Meeting, 2000. IEDM Technical Digest, International, (2000), 19-22</u>	
↓		ZHANG, H., et al., "Atomic Layer Deposition of High Dielectric Constant Nanolaminates", <u>Journal of The Electrochemical Society, 148(4), (2001), F63-F66</u>	

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DATE CONSIDERED

04/03/04